

WHAT IS CLAIMED IS:

1. A method for manufacturing a GaN-type compound semiconductor light emitting device, comprising introducing ammonia in the gaseous state into a reaction chamber housing therein a sapphire  
5 substrate, and forming a layer comprising a AlN compound started from the ammonia and organic aluminum compound gas on the substrate, wherein said ammonia is taken out in the gaseous state from a charging container, in a room temperature condition,  
10 a portion of ammonia in the charging container being in a liquid phase and another portion of ammonia in the charging container being in the gas phase, and a water concentration of said liquid phase ammonia in the charging container being controlled in the range  
15 between 0.01 and 0.5 vol ppm as determined by Fourier-transform infrared spectroscopy (FT-IR).